

# TYN20-800T

SCR

23 July 2012

Product data sheet

## 1. Product profile

### 1.1 General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT78 (TO-220AB) plastic package intended for use in applications requiring very high inrush current capability, high thermal cycling performance and high junction temperature capability ( $T_{j(max)} = 150$  °C).

### 1.2 Features and benefits

- High bidirectional blocking voltage capability
- High junction operating temperature capability
- High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability
- Very high current surge capability

### 1.3 Applications

- Capacitive Discharge Ignition (CDI)
- Crowbar protection
- Inrush protection
- Motor control
- Voltage regulation

### 1.4 Quick reference data

Table 1. Quick reference data

| Symbol       | Parameter                            | Conditions  | Min | Typ | Max | Unit |
|--------------|--------------------------------------|---|-----|-----|-----|------|
| $V_{DRM}$    | repetitive peak off-state voltage    |   | -   | -   | 800 | V    |
| $V_{RRM}$    | repetitive peak reverse voltage      |   | -   | -   | 800 | V    |
| $I_{TSM}$    | non-repetitive peak on-state current | half sine wave; $T_{j(init)} = 25$ °C; $t_p = 10$ ms; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> | -   | -   | 210 | A    |
|              |                                      | half sine wave; $T_{j(init)} = 25$ °C; $t_p = 8.3$ ms   | -   | -   | 231 | A    |
| $T_j$        | junction temperature                 |   | -   | -   | 150 | °C   |
| $I_{T(RMS)}$ | RMS on-state current                 | half sine wave; $T_{mb} \leq 129$ °C; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a>                 | -   | -   | 20  | A    |



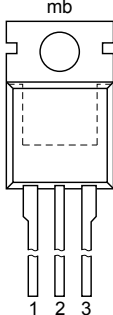

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| Symbol                         | Parameter                         | Conditions  | Min | Typ | Max | Unit             |
|--------------------------------|-----------------------------------|---|-----|-----|-----|------------------|
| <b>Static characteristics</b>  |                                   |   |     |     |     |                  |
| $I_{GT}$                       | gate trigger current              | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                                  | -   | 4.5 | 32  | mA               |
| <b>Dynamic characteristics</b> |                                   |   |     |     |     |                  |
| $dV_D/dt$                      | rate of rise of off-state voltage | $V_{DM} = 536\text{ V}$ ; $T_j = 150\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit | 300 | -   | -   | V/ $\mu\text{s}$ |

## 2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline   | Graphic symbol  |
|-----|--------|-----------------------------------|--|---|
| 1   | K      | cathode                           |  <p>TO-220AB (SOT78)</p> |  <p>sym037</p> |
| 2   | A      | anode                             |  |   |
| 3   | G      | gate                              |  |   |
| mb  | A      | mounting base; connected to anode |  |   |

## 3. Ordering information

Table 3. Ordering information

| Type number | Package  |  |         |
|-------------|----------|--|---------|
|             | Name     | Description  | Version |
| TYN20-800T  | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78   |

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol       | Parameter                         | Conditions  | Min | Max  | Unit |
|--------------|-----------------------------------|---|-----|------|------|
| $V_{DRM}$    | repetitive peak off-state voltage |   | -   | 800  | V    |
| $V_{RRM}$    | repetitive peak reverse voltage   |   | -   | 800  | V    |
| $I_{T(AV)}$  | average on-state current          | half sine wave; $T_{mb} \leq 129\text{ }^\circ\text{C}$ ; <a href="#">Fig. 3</a>                          | -   | 12.7 | A    |
| $I_{T(RMS)}$ | RMS on-state current              | half sine wave; $T_{mb} \leq 129\text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> | -   | 20   | A    |

| Symbol      | Parameter                            | Conditions   | Min | Max   | Unit             |
|-------------|--------------------------------------|--|-----|-------|------------------|
| $I_{TSM}$   | non-repetitive peak on-state current | half sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 10\text{ ms}$ ; Fig. 4; Fig. 5 | -   | 210   | A                |
|             |                                      | half sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 8.3\text{ ms}$                 | -   | 231   | A                |
| $I^2t$      | $I^2t$ for fusing                    | $t_p = 10\text{ ms}$ ; sine-wave pulse   | -   | 220.5 | A <sup>2</sup> s |
| $dl_T/dt$   | rate of rise of on-state current     | $I_T = 40\text{ A}$ ; $I_G = 200\text{ mA}$ ; $dl_G/dt = 200\text{ mA}/\mu\text{s}$  | -   | 50    | A/ $\mu\text{s}$ |
| $I_{GM}$    | peak gate current                    |  | -   | 5     | A                |
| $V_{RGM}$   | peak reverse gate voltage            |  | -   | 5     | V                |
| $P_{GM}$    | peak gate power                      |  | -   | 20    | W                |
| $P_{G(AV)}$ | average gate power                   | over any 20 ms period  | -   | 1     | W                |
| $T_{stg}$   | storage temperature                  |  | -40 | 150   | °C               |
| $T_j$       | junction temperature                 |  | -   | 150   | °C               |

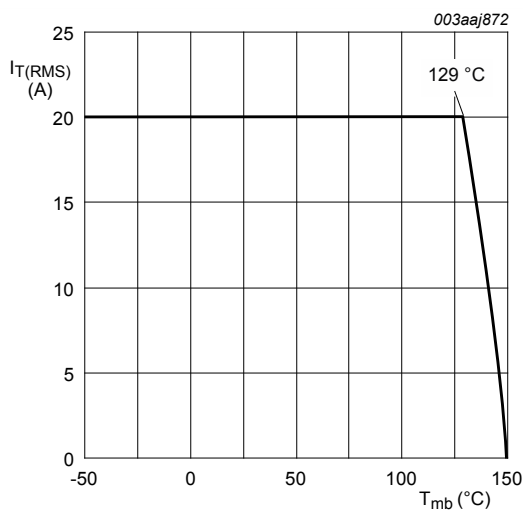


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

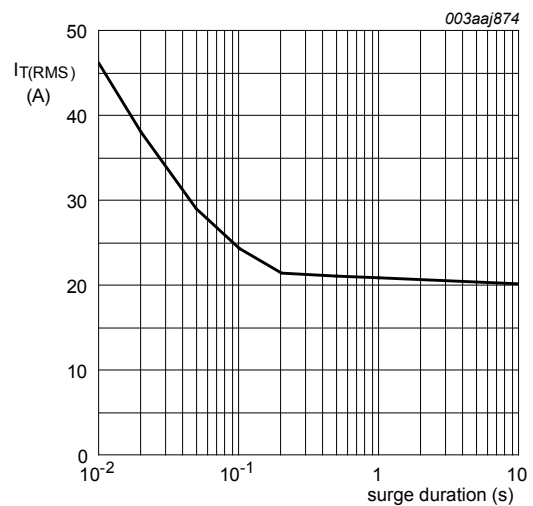


Fig. 2. RMS on-state current as a function of surge duration; maximum values

$f = 50\text{ Hz}$ ;  $T_{mb} = 129\text{ °C}$

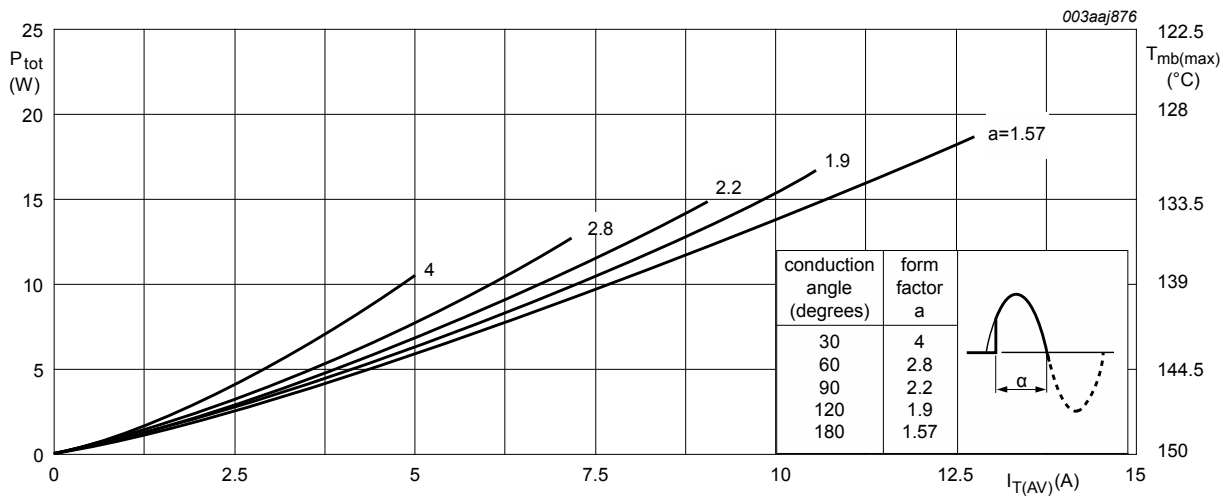


Fig. 3. Total power dissipation as a function of average on-state current; maximum values

$$a = \text{form factor} = I_{T(RMS)} / I_{T(AV)}$$

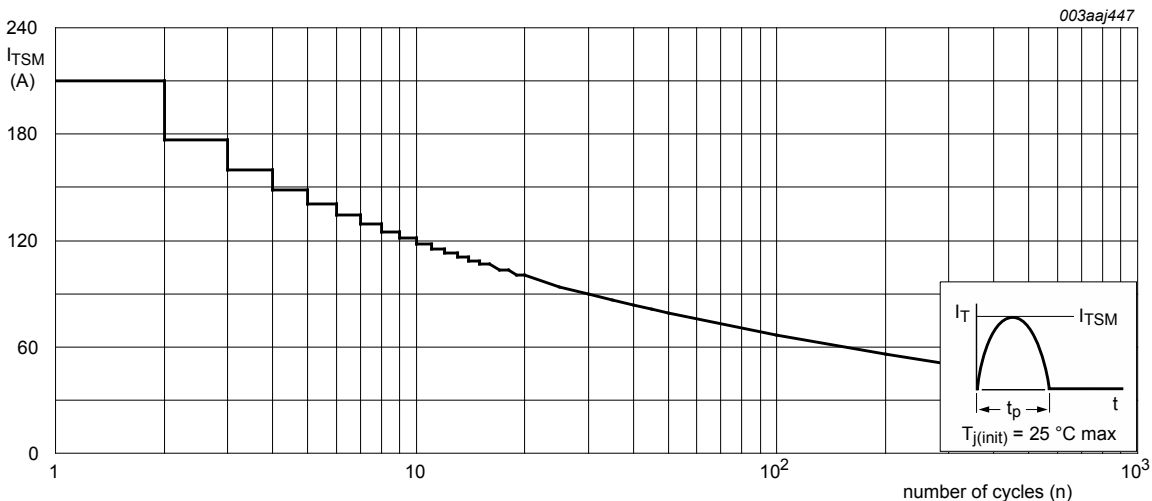
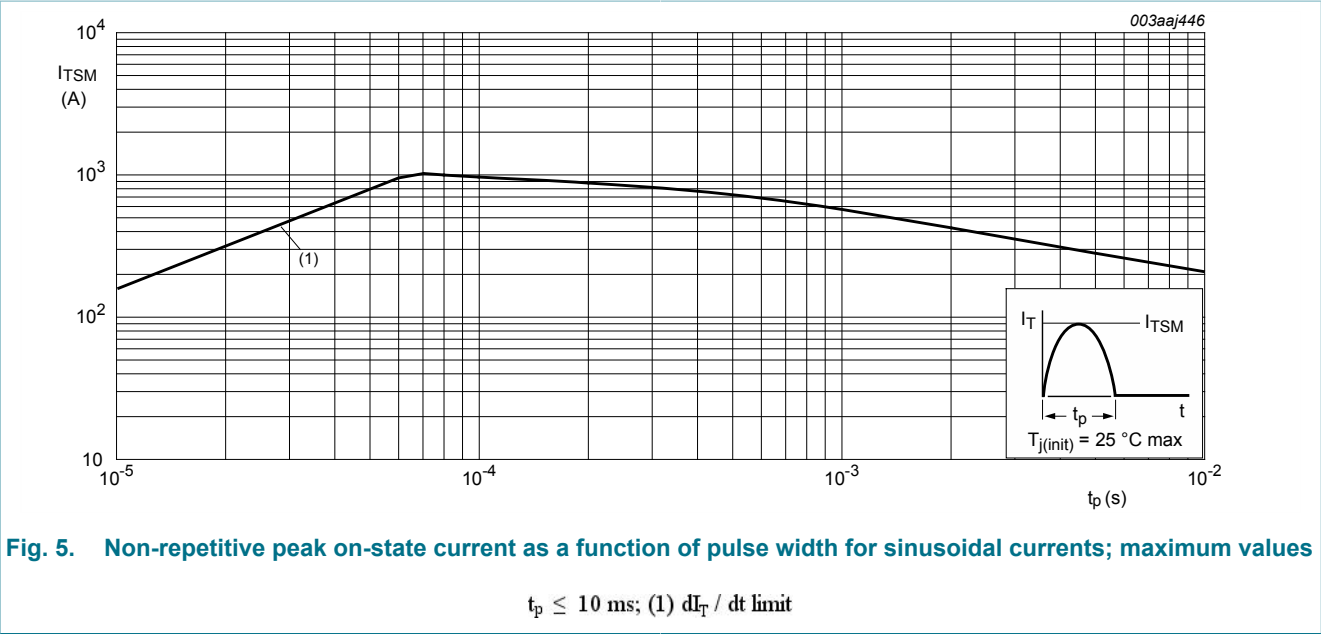


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

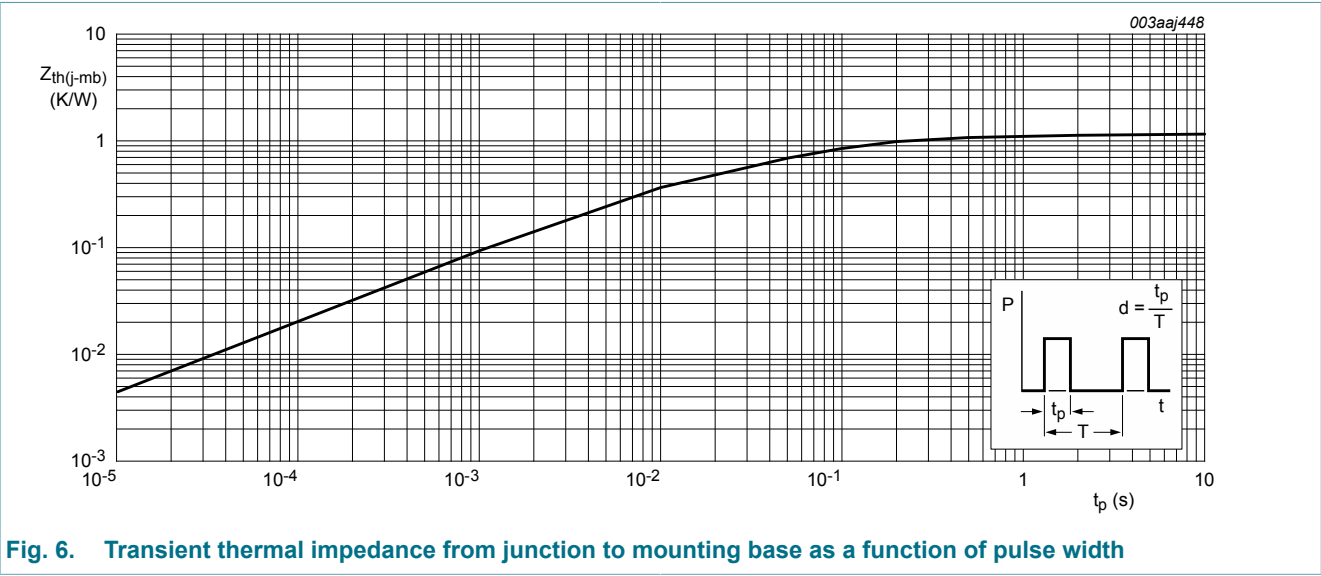
$$f = 50 \text{ Hz}$$



## 5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol         | Parameter   | Conditions             | Min | Typ | Max | Unit |
|----------------|---|------------------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | <a href="#">Fig. 6</a> | -   | -   | 1.1 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | in free air            | -   | 60  | -   | K/W  |



## 6. Characteristics

Table 6. Characteristics

| Symbol                         | Parameter                         | Conditions  | Min | Typ | Max | Unit             |
|--------------------------------|-----------------------------------|---|-----|-----|-----|------------------|
| <b>Static characteristics</b>  |                                   |   |     |     |     |                  |
| $I_{GT}$                       | gate trigger current              | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                                  | -   | 4.5 | 32  | mA               |
| $I_L$                          | latching current                  | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                                  | -   | 21  | 60  | mA               |
| $I_H$                          | holding current                   | $V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>   | -   | 16  | 40  | mA               |
| $V_T$                          | on-state voltage                  | $I_T = 32\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>  | -   | 1.2 | 1.5 | V                |
| $V_{GT}$                       | gate trigger voltage              | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>                                 | -   | 0.7 | 1.3 | V                |
|                                |                                   | $V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 150\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>                               | 0.2 | 0.4 | -   | V                |
| $I_D$                          | off-state current                 | $V_D = 800\text{ V}$ ; $T_j = 150\text{ }^\circ\text{C}$  | -   | 0.2 | 1   | mA               |
| $I_R$                          | reverse current                   | $T_j = 150\text{ }^\circ\text{C}$ ; $V_R = 800\text{ V}$  | -   | 0.2 | 1   | mA               |
| <b>Dynamic characteristics</b> |                                   |   |     |     |     |                  |
| $dV_D/dt$                      | rate of rise of off-state voltage | $V_{DM} = 536\text{ V}$ ; $T_j = 150\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit | 300 | -   | -   | V/ $\mu\text{s}$ |

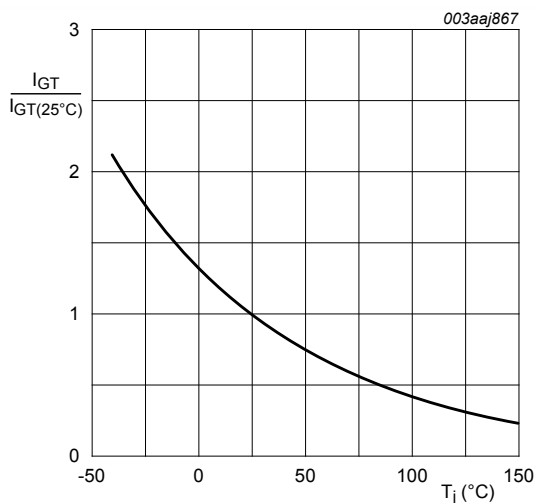


Fig. 7. Normalized gate trigger current as a function of junction temperature

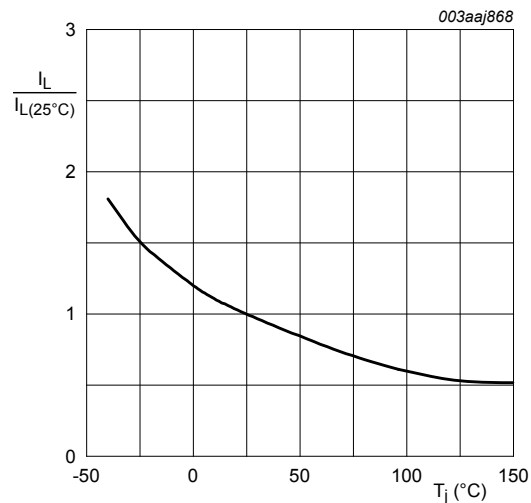


Fig. 8. Normalized latching current as a function of junction temperature

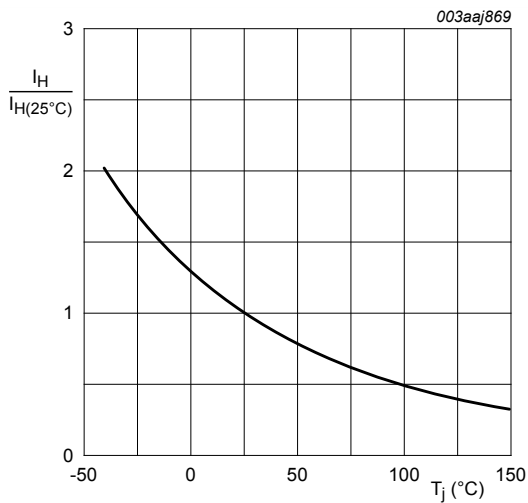
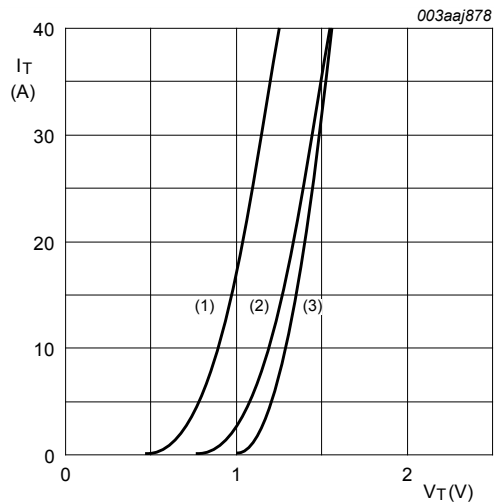


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 1.0485\text{ V}$ ;  $R_s = 0.0133\ \Omega$   
(1)  $T_J = 150^\circ\text{C}$ ; typical values  
(2)  $T_J = 150^\circ\text{C}$ ; maximum values  
(3)  $T_J = 25^\circ\text{C}$ ; maximum values

Fig. 10. On-state current as a function of on-state voltage

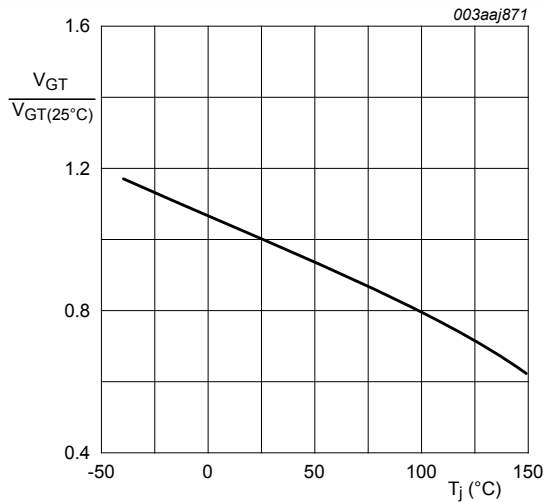


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

7. Package outline

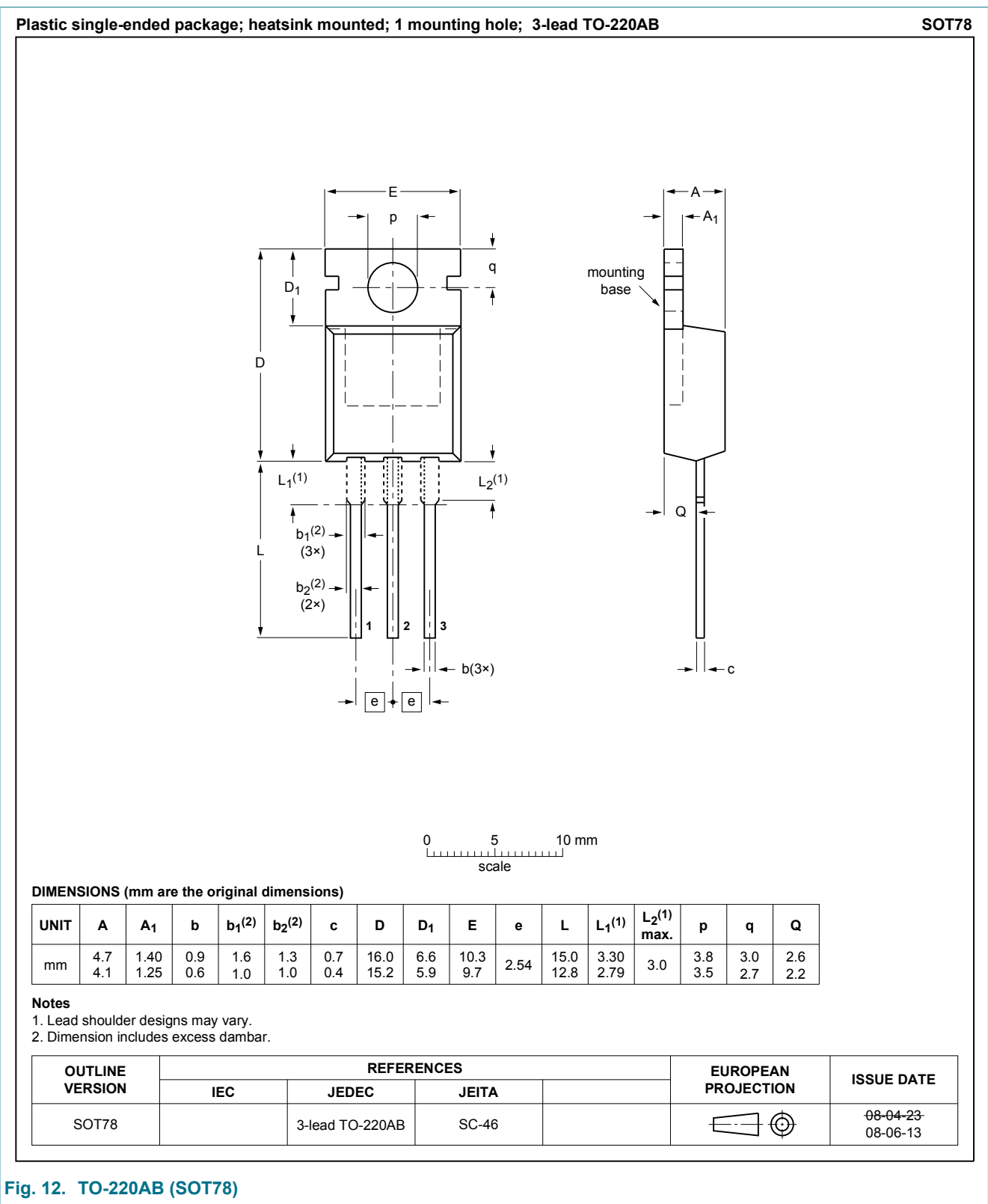


Fig. 12. TO-220AB (SOT78)



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|--------------------------------|--------------------|---|
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